

Process Change Notification

Date: July 19, 2013
PCN Reference: S20152 Rev 2 (added lead finish)
PCR Reference:
Product Reference: 3.3x3.3 PQFN dual MOSFET

To Our Valued Customer:

As always we appreciate your use of International Rectifier semiconductor products. Our commitment to customer satisfaction and continuous improvement is demonstrated by our change plans to enhance capacity, quality and reliability. This notice is to inform you of the following change:

Type of Change Notification:

Alternate site for the assembly of the product listed in the following page.

Description of Change:

GEM (China) has been qualified as alternate assembly site for the Products identified in the following page. The Bill of Materials in the new assembly site will be as follows:

- Equivalent dual pad PQFN leadframe
- Sumitomo G600-series mold compound
- Kyocera CT200-series die attach Ag epoxy
- Lead Finish – Ni/Pd/Au

Reason for the Change:

Additional assembly capacity

Effect Date:

August 31, 2013

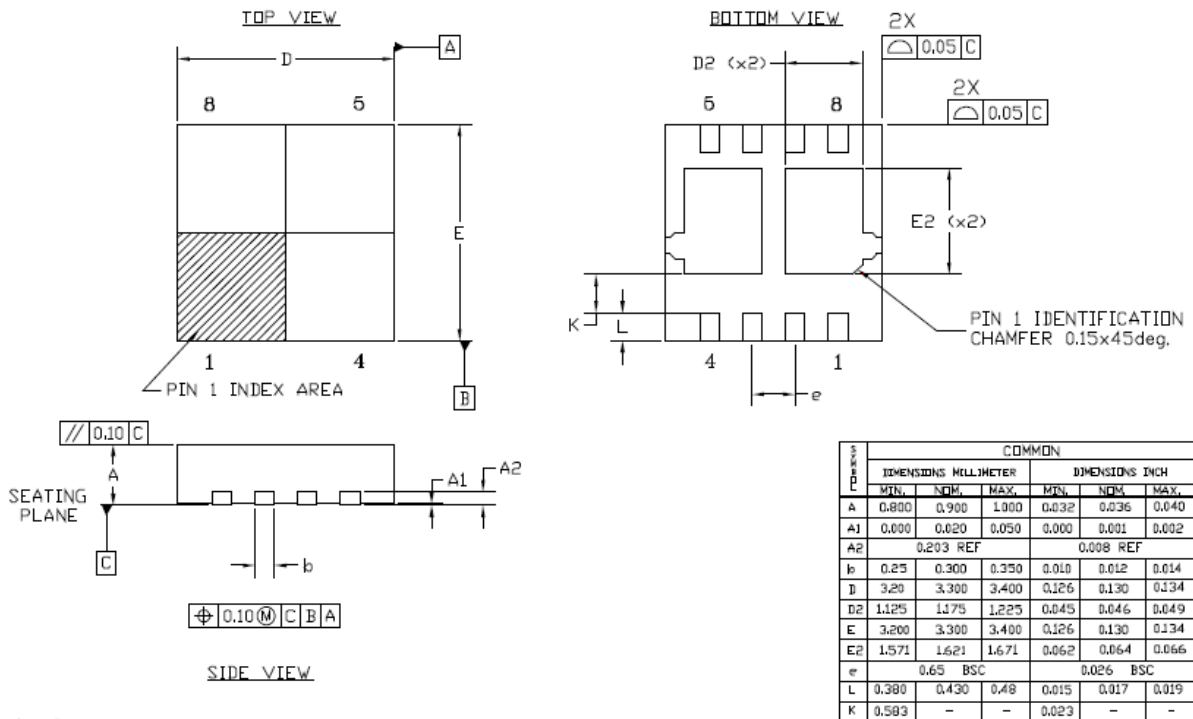


International Rectifier will consider this change approved and will implement it by the effective date unless specific conditions of acceptance or data requests are provided in writing within 10 days of receipt of this notice. Please submit conditions of acceptance and data requests to the PCN coordinator listed at the end of this notice.

Impact of Change:

While the products out of the new site will have no fit or function change, the form is changing a bit due to footprint changes. Although different, the new footprint is compatible with the old one, see below comparison for more details:

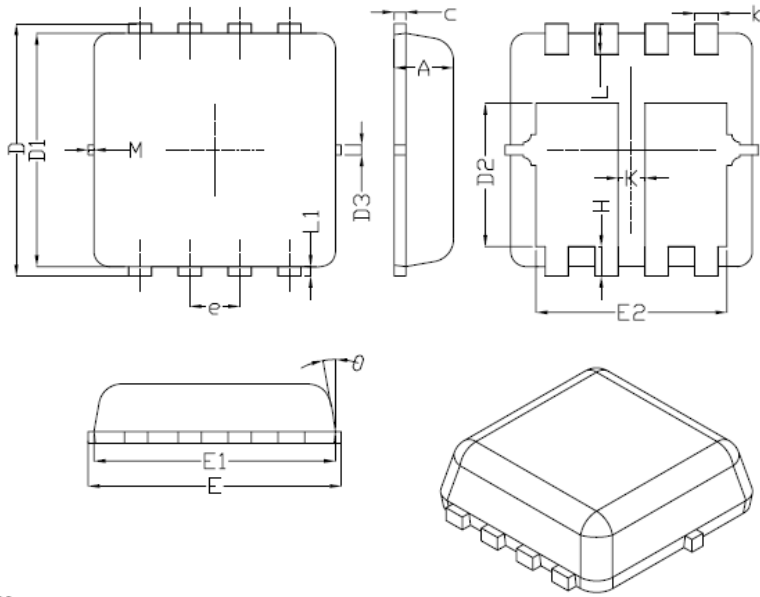
Hana (current assembly site):



NOTES :



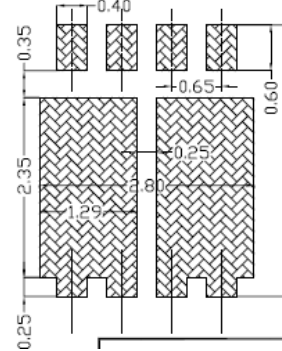
GEM (alternate assembly site):



| SYMBOL | DIMENSIONAL REQSmts | | |
|--------|---------------------|------|------|
| | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 |
| b | 0.25 | 0.30 | 0.33 |
| c | 0.10 | 0.15 | 0.25 |
| D | 3.25 | 3.35 | 3.45 |
| D1 | 3.00 | 3.10 | 3.20 |
| D2 | 1.78 | 1.88 | 1.98 |
| D3 | --- | 0.13 | --- |
| E | 3.20 | 3.30 | 3.40 |
| E1 | 3.00 | 3.15 | 3.20 |
| E2 | 2.39 | 2.49 | 2.59 |
| e | 0.55BSC | | |
| H | 0.30 | 0.39 | 0.50 |
| L | 0.30 | 0.40 | 0.50 |
| L1 | --- | 0.13 | --- |
| K | 0.30 | --- | --- |
| theta | --- | 10° | 12° |
| M | * | * | 0.13 |

Land Pattern

(Only for Reference)



Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.

Products Affected:

| Part Number | Description |
|----------------|---|
| IRFHM792TRPBF | 100V Dual N-Channel HEXFET Power MOSFET |
| IRFHM792TR1PBF | 100V Dual N-Channel HEXFET Power MOSFET |
| 62-0217PBF | 100V Dual N-Channel HEXFET Power MOSFET |

Qualification:

Parts passed all the reliability testing requirements. Reliability qualification report is available upon request. Qualification standards can be found on International Rectifier’s web site at www.irf.com/product-info/reliability.

Data Availability:

Please contact the PCN Coordinator for supporting data.

Contact Information:

| CONTACT TYPE | NAME | PHONE | EMAIL |
|-----------------|-----------------|--------------|------------------|
| PCN Coordinator | John Michaelson | 951 375-4432 | jmichae2@irf.com |
| Technical | Mario Dolores | +6635350803 | mdolore1@irf.com |